

## N-Channel 30 V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
30	0.0055 at V <sub>GS</sub> = 10 V	25	13.8 nC
	0.0076 at V <sub>GS</sub> = 4.5 V	21	

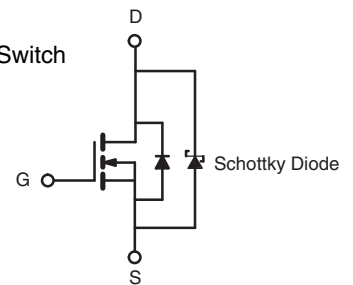
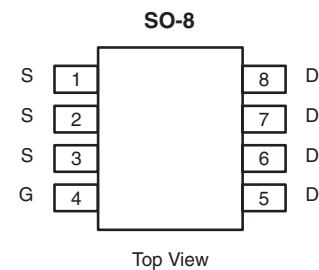
### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET<sup>®</sup> Monolithic TrenchFET<sup>®</sup> Power MOSFET and Schottky Diode
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



### APPLICATIONS

- Notebook PC
  - System Power
- VRM, POL, Server
- Synchronous Rectifier Switch



Ordering Information: Si4752DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	25	
		T <sub>C</sub> = 70 °C	20	
		T <sub>A</sub> = 25 °C	17.4 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	13.8 <sup>b, c</sup>	
Pulsed Drain Current (300 μs)	I <sub>DM</sub>	80	A	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C		5.6
		T <sub>A</sub> = 25 °C		2.7 <sup>b, c</sup>
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>		20
Single Pulse Avalanche Energy		E <sub>AS</sub>	20	mJ
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	6.25	
		T <sub>C</sub> = 70 °C	4.0	
		T <sub>A</sub> = 25 °C	3.0 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.9 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	33	42	°C/W
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	16	20	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 85 °C/W.

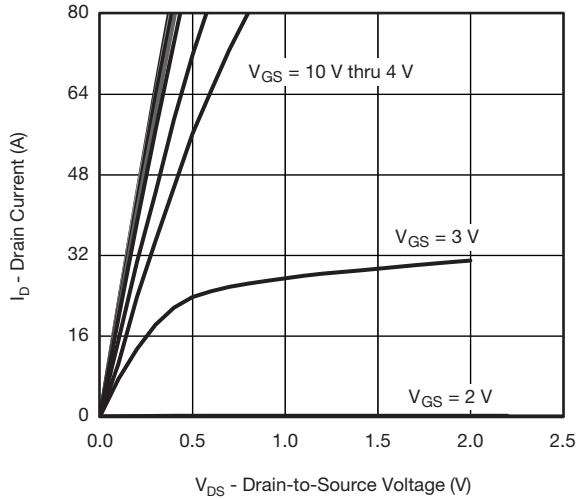
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1.0		2.2	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$		0.018	0.15	mA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$		2.0	20	
On -State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.0045	0.0055	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$		0.0063	0.0076	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		45		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1700		pF
Output Capacitance	$C_{oss}$			410		
Reverse Transfer Capacitance	$C_{rss}$			130		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		28.5	43	nC
				13.8	21	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		4.2		
Gate-Drain Charge	$Q_{gd}$			3.8		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.3	1.4	2.8	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		18	35	ns
Rise Time	$t_r$			15	30	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	$t_f$			8	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		11	22	
Rise Time	$t_r$			12	24	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	$t_f$			8	16	
<b>Drain-Source Body Diode and Schottky Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			5.6	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				80	
Body Diode Voltage	$V_{SD}$	$I_S = 3\text{ A}$		0.46	0.65	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		23	45	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			12	24	nC
Reverse Recovery Fall Time	$t_a$			11		ns
Reverse Recovery Rise Time	$t_b$			12		

## Notes:

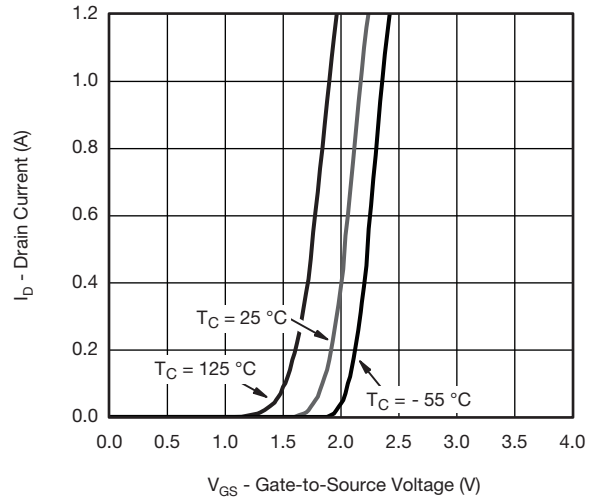
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

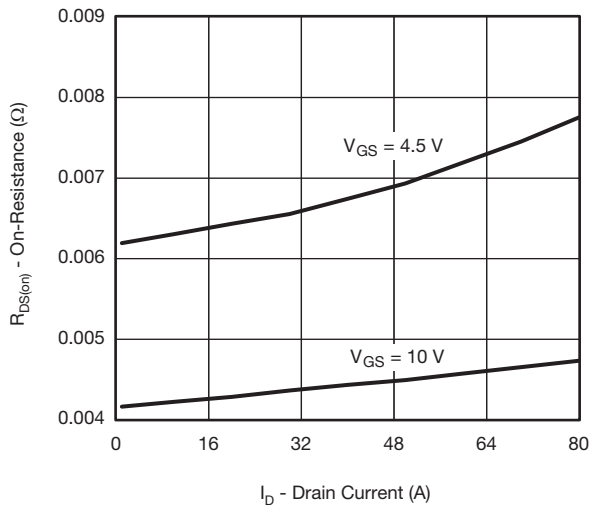
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



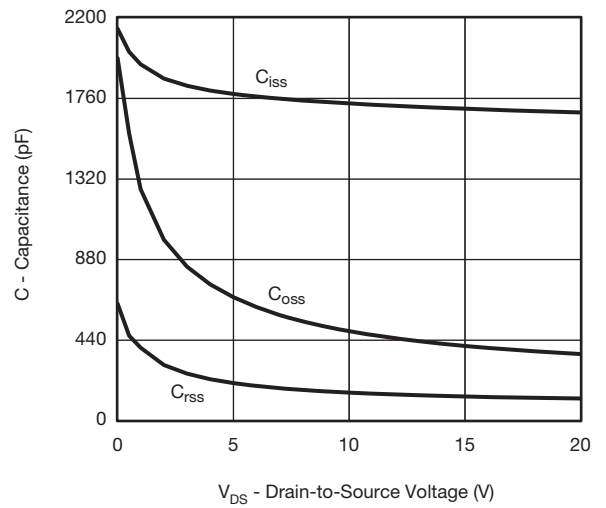
**Output Characteristics**



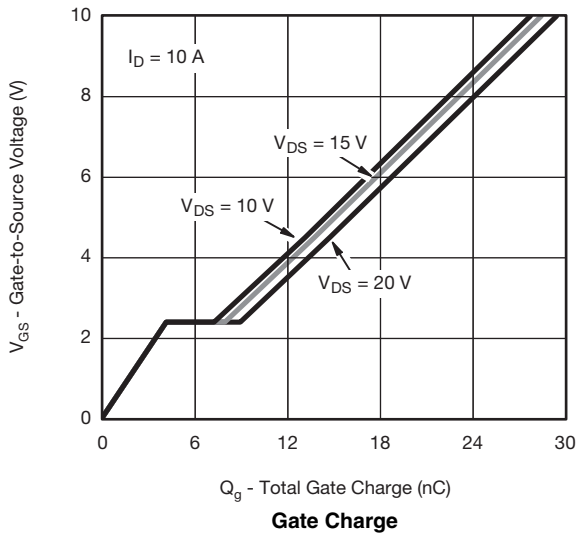
**Transfer Characteristics**



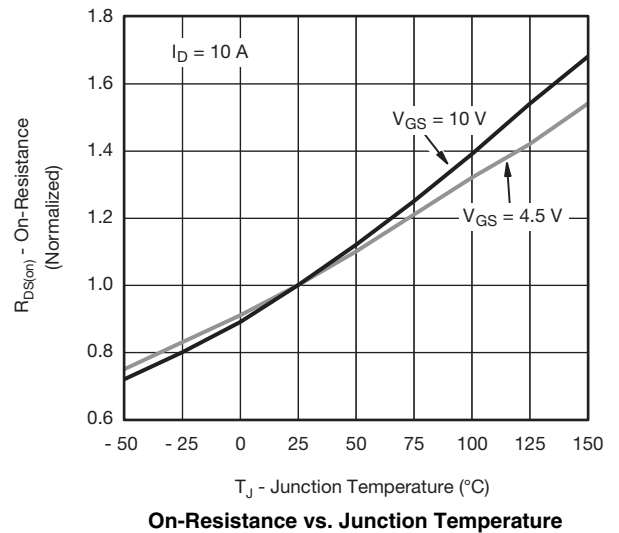
**On-Resistance vs. Drain Current**



**Capacitance**

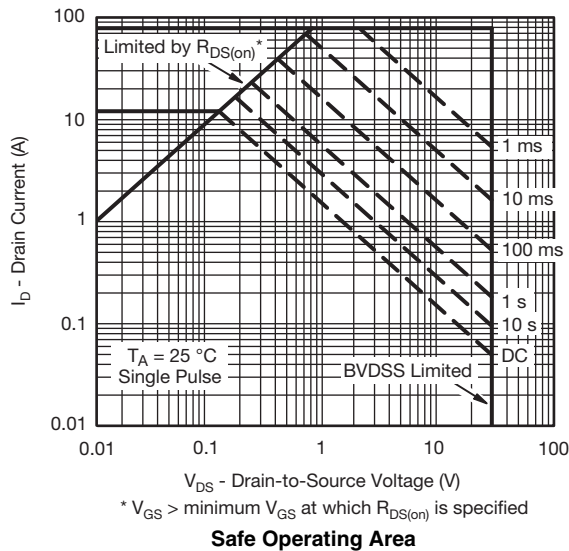
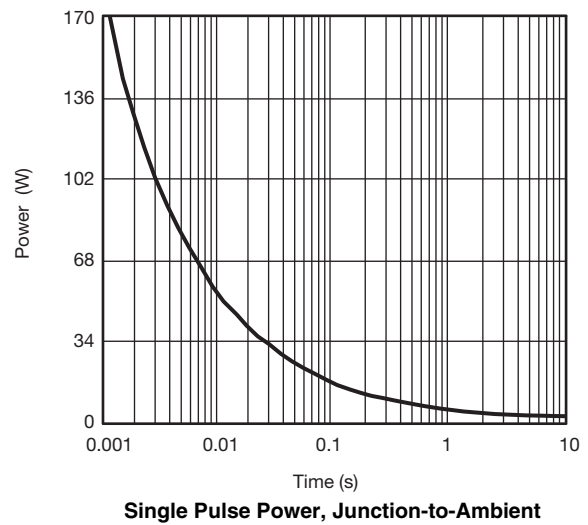
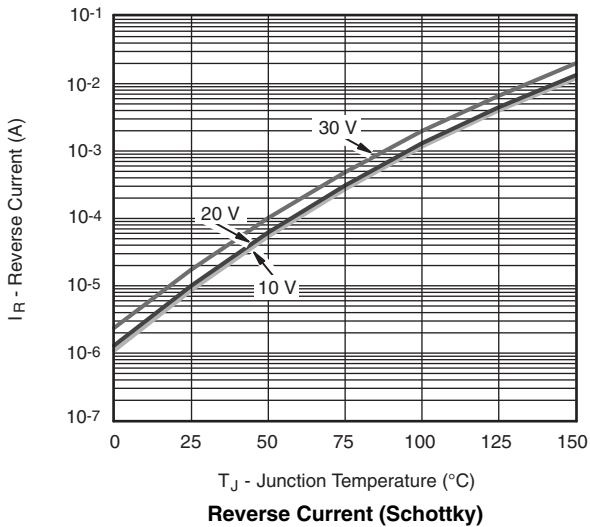
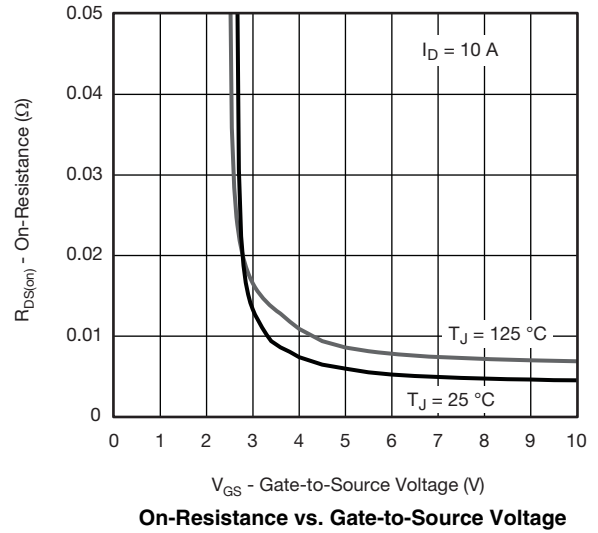
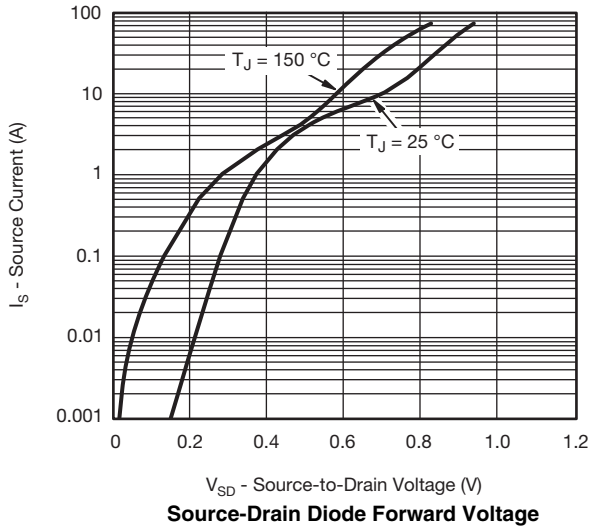


**Gate Charge**

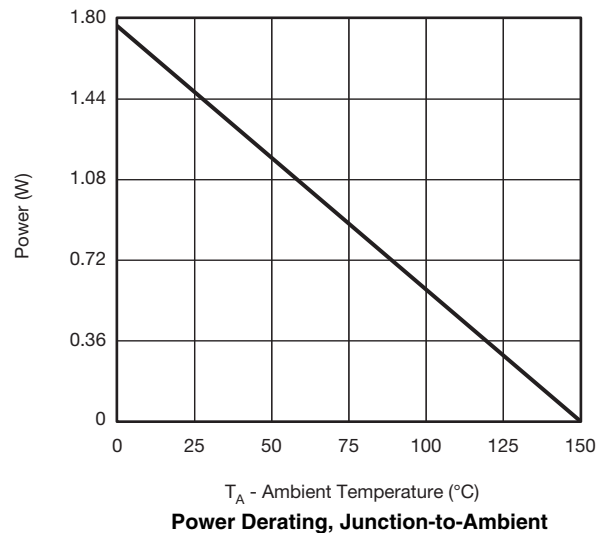
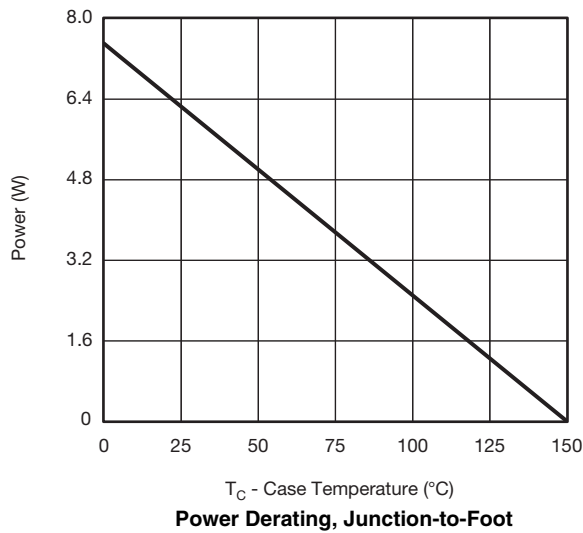
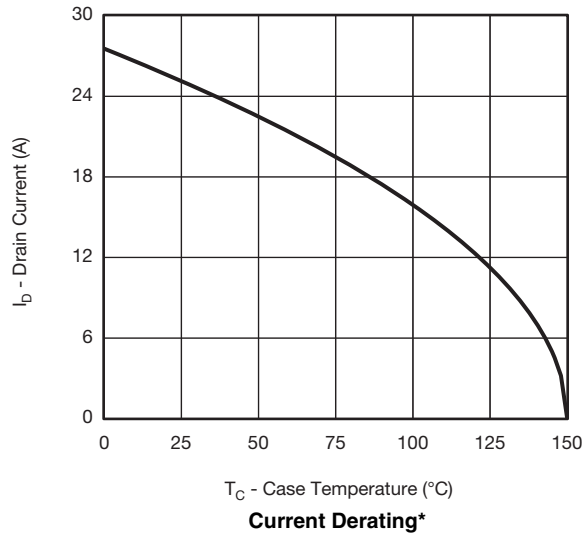


**On-Resistance vs. Junction Temperature**

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

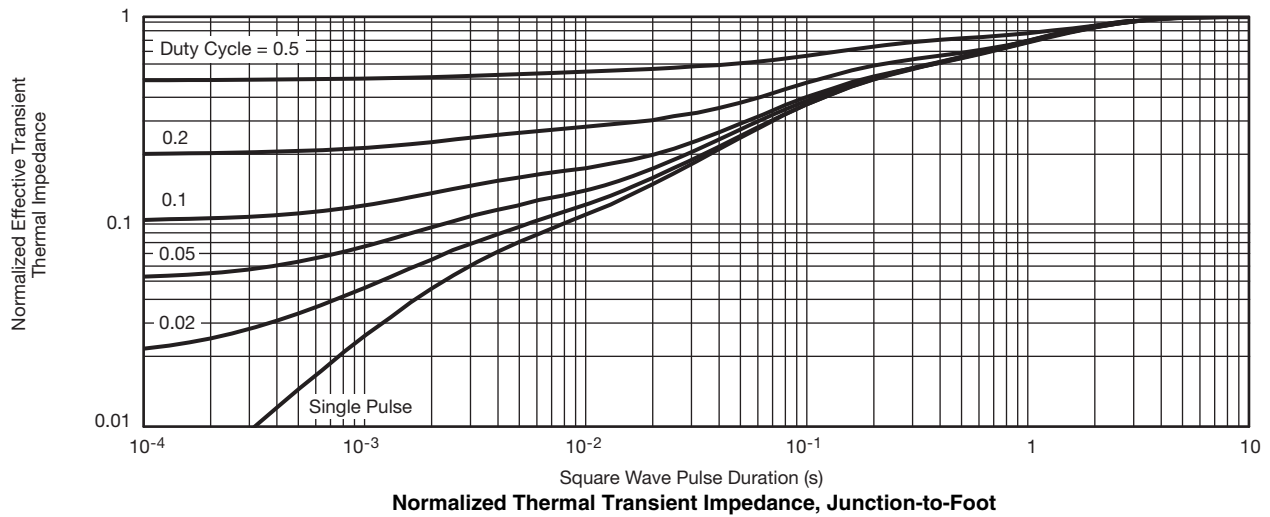
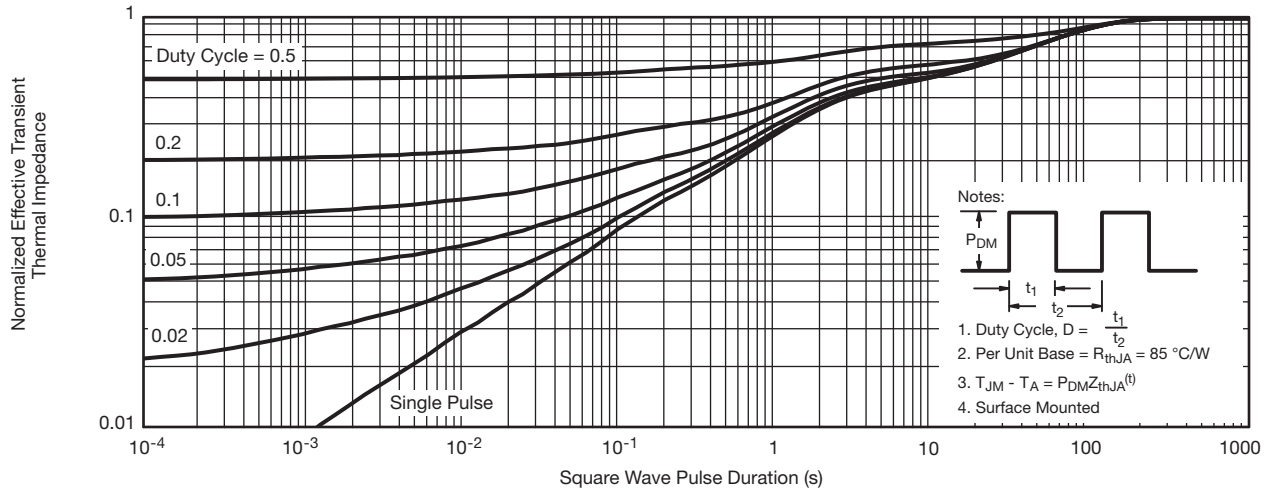


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



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